Complementary Silicon Power Plastic Transistors

. . . designed for low voltage, low-power, high-gain audio amplifier applications.

• Collector-Emitter Sustaining Voltage —

VCEO(sus) = 25 Vdc (Min) @ IC = 10 mAdc

High DC Current Gain — hFE = 70 (Min) @ IC = 500 mAdc

= 45 (Min) @ IC = 2.0 Adc

= 10 (Min) @ I_C = 5.0 Adc

• Low Collector-Emitter Saturation Voltage -

VCE(sat) = 0.3 Vdc (Max) @ IC = 500 mAdc

= 0.75 Vdc (Max) @ IC = 2.0 Adc

• High Current-Gain — Bandwidth Product —

fT = 65 MHz (Min) @ IC = 100 mAdc
• Annular Construction for Low Leakage —

ICBO = 100 nAdc @ Rated VCB

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CB}	40	Vdc
Collector–Emitter Voltage	V _{CEO}	25	Vdc
Emitter-Base Voltage	V _{EB}	8.0	Vdc
Collector Current — Continuous Peak	IC	5.0 10	Adc
Base Current	ΙΒ	1.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	15 0.12	Watts W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	PD	1.5 0.012	Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	8.34	°C/W
Thermal Resistance, Junction to Ambient	θЈА	83.4	°C/W

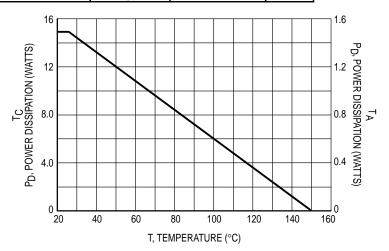


Figure 1. Power Derating

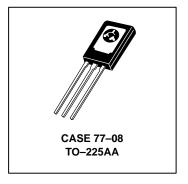
Preferred devices are Motorola recommended choices for future use and best overall value.

REV 7

MJE200* PNP MJE210*

*Motorola Preferred Device

5 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
25 VOLTS
15 WATTS





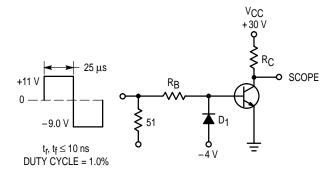
MJE200 MJE210

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					•
Collector–Emitter Sustaining Voltage (1) (I _C = 10 mAdc, I _B = 0)		VCEO(sus)	25	_	Vdc
Collector Cutoff Current $(V_{CB} = 40 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 40 \text{ Vdc}, I_E = 0, T_J = 125^{\circ}C)$		ICBO		100 100	nAdc μAdc
Emitter Cutoff Current (V _{BE} = 8.0 Vdc, I _C = 0)		IEBO	_	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (1) (I _C = 500 mAdc, V _{CE} = 1.0 Vdc) (I _C = 2.0 Adc, V _{CE} = 1.0 Vdc) (I _C = 5.0 Adc, V _{CE} = 2.0 Vdc)		hFE	70 45 10	— 180 —	_
Collector-Emitter Saturation Voltage (1) (IC = 500 mAdc, I _B = 50 mAdc) (IC = 2.0 Adc, I _B = 200 mAdc) (IC = 5.0 Adc, I _B = 1.0 Adc)		VCE(sat)	_ _ _ _	0.3 0.75 1.8	Vdc
Base–Emitter Saturation Voltage (1) (I _C = 5.0 Adc, I _B = 1.0 Adc)		V _{BE(sat)}	_	2.5	Vdc
Base–Emitter On Voltage (1) (I _C = 2.0 Adc, V _{CE} = 1.0 Vdc)		V _{BE(on)}	_	1.6	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (2) ($I_C = 100 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f_{test} = 10 \text{ MHz}$)		fΤ	65	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	MJE200 MJE210	C _{ob}	_ 	80 120	pF

⁽¹⁾ Pulse Test: Pulse Width = 300 μ s, Duty Cycle \approx 2.0%.

⁽²⁾ $f_T = |h_{fe}| \cdot f_{test}$



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS D $_1$ MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE $I_B\approx 100$ mA MSD6100 USED BELOW $I_B\approx 100$ mA

Figure 2. Switching Time Test Circuit

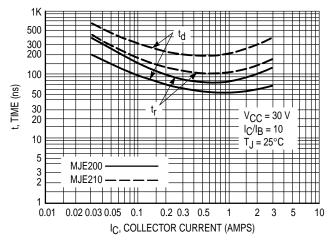


Figure 3. Turn-On Time

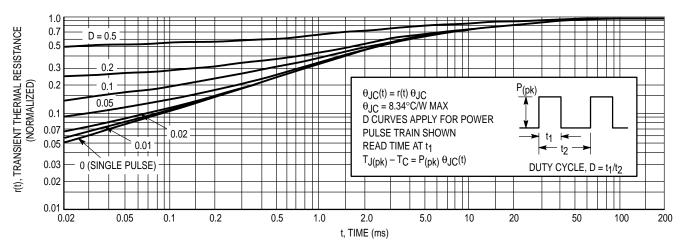


Figure 4. Thermal Response

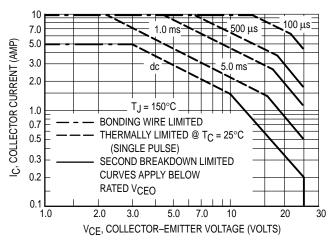


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

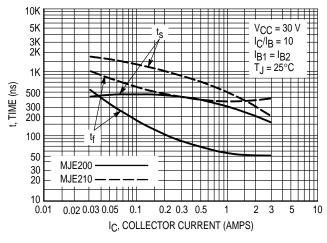


Figure 6. Turn-Off Time

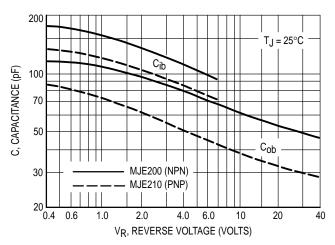


Figure 7. Capacitance

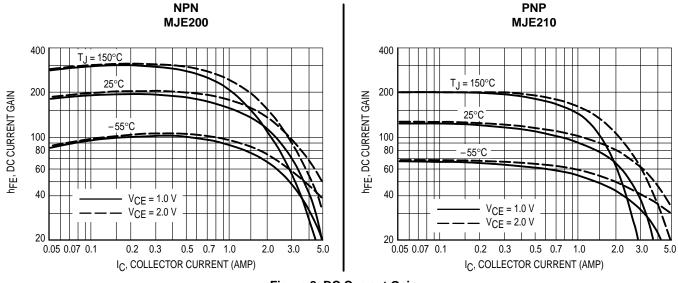


Figure 8. DC Current Gain

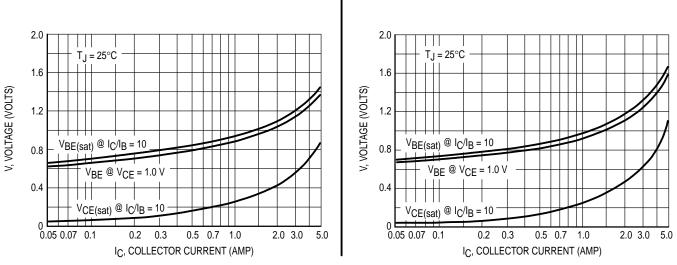


Figure 9. "On" Voltage

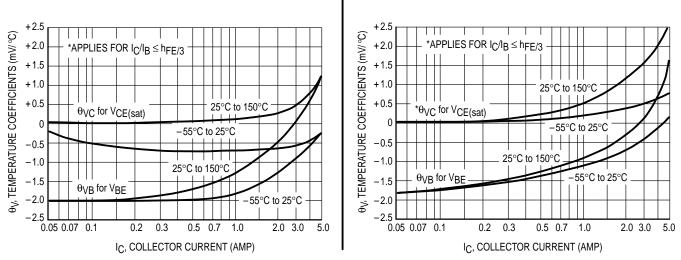
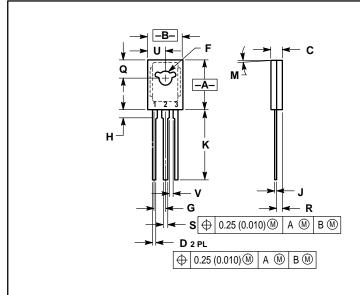


Figure 10. Temperature Coefficients

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.425	0.435	10.80	11.04
В	0.295	0.305	7.50	7.74
С	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094	0.094 BSC		BSC
Н	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.055	1.15	1.39
S	0.025	0.035	0.64	88.0
U	0.145	0.155	3.69	3.93
٧	0.040		1.02	

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

CASE 77-08 TO-225AA **ISSUE V**

MJE200 MJE210

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How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



